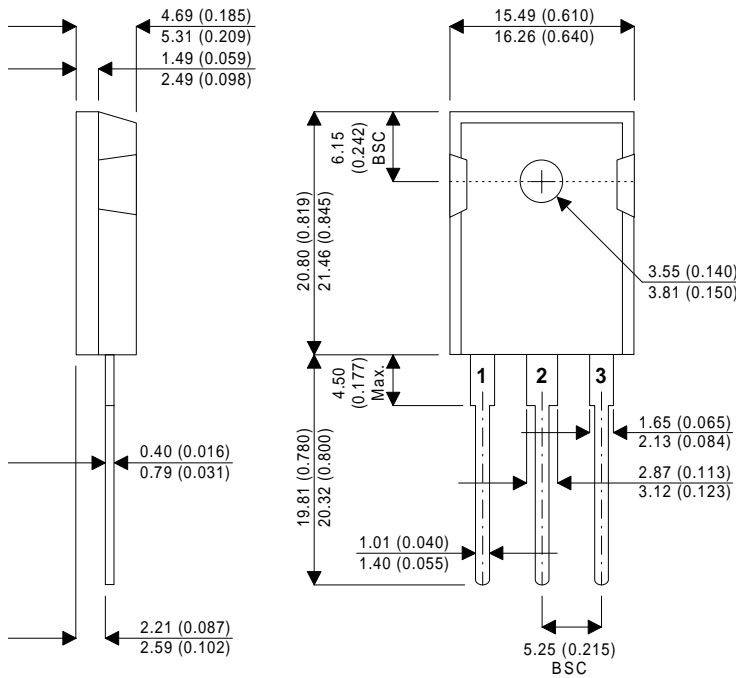


MECHANICAL DATA

Dimensions in mm (inches)



TO-247

Pin 1 – Gate

Pin 2 – Source

Pin 3 – Drain

**N-CHANNEL
POWER MOSFET**

**POWER MOSFETS FOR
AUDIO APPLICATIONS**

FEATURES

- HIGH SPEED SWITCHING
- N-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P-CHANNEL ALSO AVAILABLE AS BUZ905P & BUZ906P

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}C$ unless otherwise stated)

| | | BUZ900P | BUZ901P |
|-----------------|--|----------------|----------------|
| V_{DSX} | Drain – Source Voltage | 160V | 200V |
| V_{GSS} | Gate – Source Voltage | ±14V | |
| I_D | Continuous Drain Current | 8A | |
| $I_{D(PK)}$ | Body Drain Diode | 8A | |
| P_D | Total Power Dissipation @ $T_{case} = 25^{\circ}C$ | 125W | |
| T_{stg} | Storage Temperature Range | -55 to 150°C | |
| T_j | Maximum Operating Junction Temperature | 150°C | |
| $R_{\theta JC}$ | Thermal Resistance Junction – Case | 1.0°C/W | |

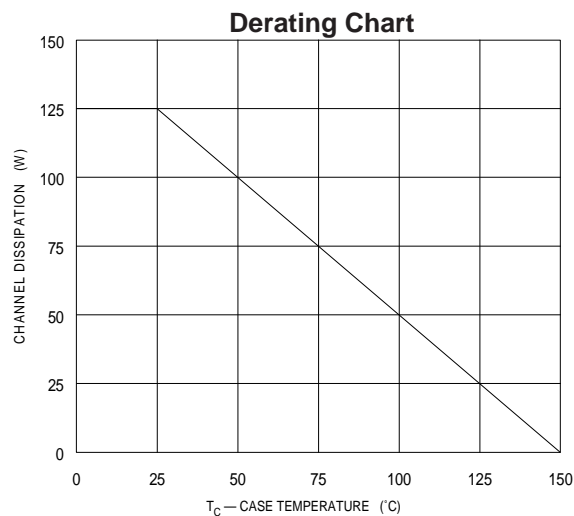
STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

| Characteristic | | Test Conditions | | Min. | Typ. | Max. | Unit |
|-----------------------|-----------------------------------|---|-----------------------------------|------|------|------|------|
| BV _{DSX} | Drain – Source Breakdown Voltage | V _{GS} = -10V I _D = 10mA | BUZ900P | 160 | | | V |
| | | | BUZ901P | 200 | | | |
| BV _{GSS} | Gate – Source Breakdown Voltage | V _{DS} = 0 | I _G = ±100µA | ±14 | | | V |
| V _{GS(OFF)} | Gate – Source Cut-Off Voltage | V _{DS} = 10V | I _D = 100mA | 0.15 | | 1.5 | V |
| V _{DS(SAT)*} | Drain – Source Saturation Voltage | V _{GD} = 0 | I _D = 8A | | | 12 | V |
| I _{DSX} | Drain – Source Cut-Off Current | V _{GS} = -10V | V _{DS} = 160V BUZ900P | | | 10 | mA |
| | | | V _{DS} = 200V BUZ901P | | | 10 | |
| yfs* | Forward Transfer Admittance | V _{DS} = 10V | I _D = 3A | 0.7 | | 2 | S |

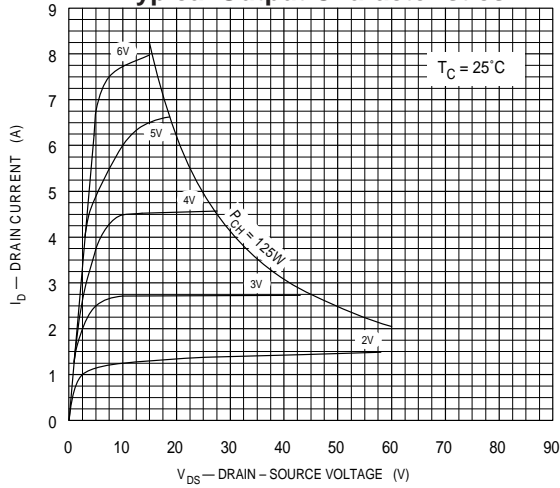
DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

| Characteristic | | Test Conditions | | Min. | Typ. | Max. | Unit | |
|------------------|------------------------------|-----------------------------------|--|------|------|------|------|--|
| C _{iss} | Input Capacitance | V _{DS} = 10V f = 1MHz | | | 500 | | pF | |
| C _{oss} | Output Capacitance | | | | | 300 | | |
| C _{rss} | Reverse Transfer Capacitance | | | | | 10 | | |
| t _{on} | Turn-on Time | V _{DS} = 20V | | | 100 | | ns | |
| t _{off} | Turn-off Time | I _D = 5A | | | 50 | | | |

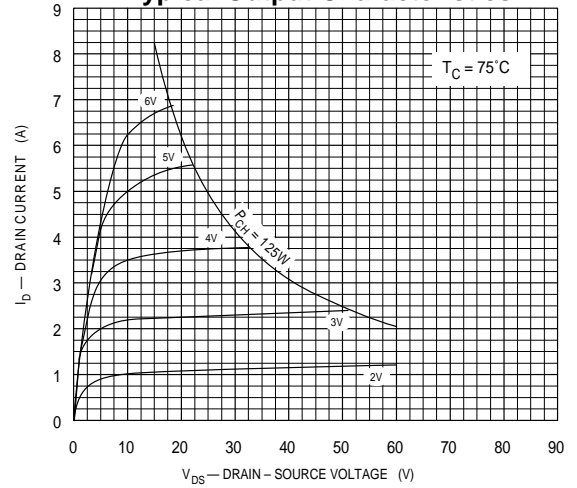
* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.



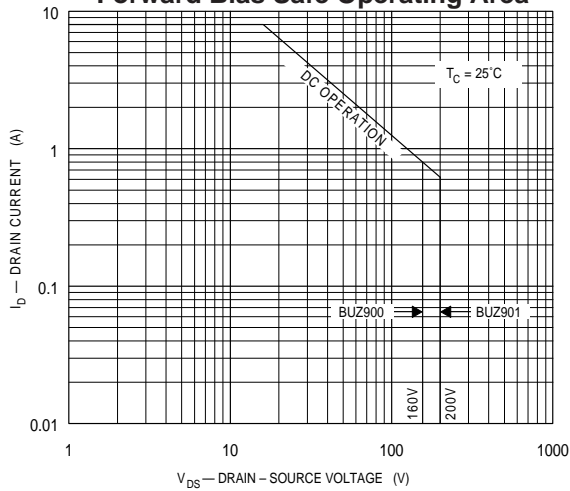
Typical Output Characteristics



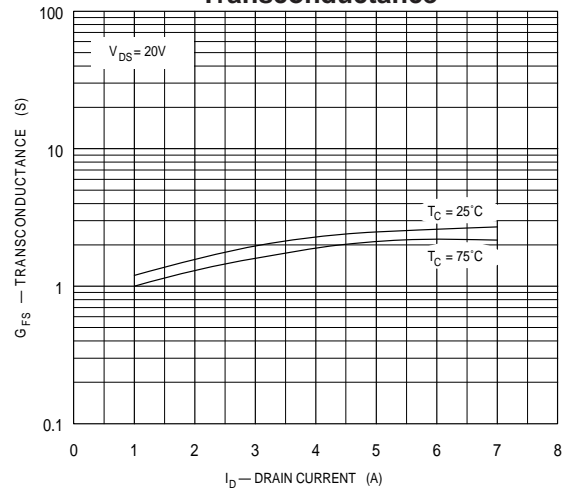
Typical Output Characteristics



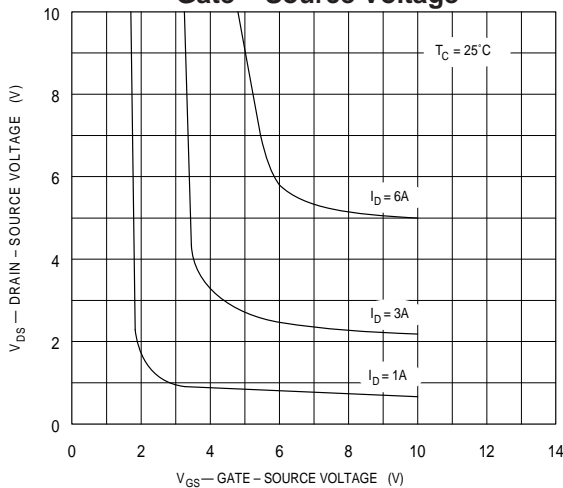
Forward Bias Safe Operating Area



Transconductance



Drain - Source Voltage vs Gate - Source Voltage



Typical Transfer Characteristics

